

CLAIM AMENDMENTS

1. (Currently Amended) An integrated circuit device comprising:
a semiconductor amplification element supplied with a voltage from a first power source; and
a bias circuit for applying a bias voltage to the semiconductor amplification element,
wherein
~~a power source of the bias circuit is supplied with a second voltage from a~~
second power source,
~~the second power source is connected to a the first power source of the~~
~~semiconductor amplification element via a semiconductor element such that, and~~
idle current of the semiconductor amplification element ~~is changed~~ changes in
response to ~~a change of a supply~~ the voltage of supplied by the first power source to the
semiconductor amplification element.
2. (Previously Presented) The integrated circuit device according to Claim 1, wherein
the semiconductor element is a transistor.
3. (Previously Presented) The integrated circuit device according to Claim 1, wherein
the semiconductor element is a diode.
4. (Currently Amended) The integrated circuit device according to Claim 1, which acts
as a power amplifier circuit, including a transistor as the semiconductor amplification element,
wherein the bias circuit includes a bias generating circuit for generating a base bias of the
transistor and a temperature compensation circuit for temperature compensation of the bias
generating circuit.